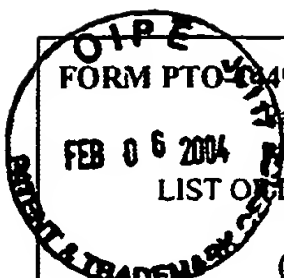
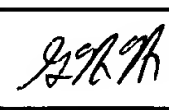



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				U.S. Department of Commerce Patent and Trademark Office		Attorney Docket Number: 5308-156		Serial No.: 09/911,995	
						Applicants: Ryu et al.			
						Filing Date: July 24, 2001		Group: 2811	
U. S. PATENT DOCUMENTS									
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate		
FOREIGN PATENT DOCUMENTS									
		Document Number	Date	Country	Class	Subclass	Translation Yes No		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									
	1	Williams et al., "Passivation of the 4-H SiC/SiO ₂ Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.							
	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.							

EXAMINER
EXAMINERG. MUNSONDATE CONSIDERED 24 August 2004

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.